This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of claims:

1. (Canceled)

2. (Canceled)

3. (Canceled)

4. (Previously presented) An etching solution according to Claim 17 , wherein said solvent mixture consists essentially of ethylene glycol and glycerol in a mixing ratio of from 1:10 to 10:1.

5. (Previously presented) An etching solution according to Claim 17, wherein said solvent mixture consists essentially of ethylene glycol and glycerol in a mixing ratio of from 1:5 to 5:1.

6. (Canceled)

7. (Previously presented) An etching solution according to Claim 17, wherein the individual components are of high-purity.

8. (Withdrawn and Amended) A method for the selective etching of a doped silicate ~~layers~~ layer with respect to a thermal oxide layer comprising treating said doped silicate ~~layers~~ layer with an etching solution according to Claim 17.

9. (Withdrawn) A method according to claim 8, wherein said doped silicate is boron doped glass.

10. (Withdrawn) A method according to claim 8, wherein said doped silicate is phosphorous doped glass.

11. (Withdrawn) A method according to claim 8, wherein said doped silicate is boron-phosphorous doped glass.

12. (Withdrawn) A method according to claim 8, wherein said selective etching is carried out in a spin etcher.

13. (Withdrawn) A method according to claim 8, wherein said selective etching is carried out in a drip etcher.

14. (Previously presented) An etching solution according to Claim 17, wherein the amount of said water is 6.4 -20 % by weight.

15. (Canceled)

16. (Canceled)

17. (Currently Amended) An etching solution for the production of integrated circuits consisting essentially of
5- 20% by weight hydrofluoric acid,
a solvent mixture consisting essentially of at least two of ethylene glycol, propylene glycol, ethanol, and glycerol,
and
1-20 % by weight water,
said solution having the property of etching the doped oxide BSG at a much higher rate than it etches thermal oxide, thus being capable of essentially not etching thermal oxide while etching said doped oxide.

18. (Previously presented) An etching solution according to claim 17, wherein the amount of hydrofluoric acid is 10- 20% by weight .

19. (Previously presented) An etching solution according to claim 17, wherein the amount of hydrofluoric acid is 15- 20% by weight .

20. (New) An combination comprising

(a) an etching solution for the selective etching of doped silicate layers consisting essentially of

5- 20% by weight hydrofluoric acid,

a solvent mixture consisting essentially of at least two of ethylene glycol, propylene glycol, ethanol, and glycerol,

and

1-20 % by weight water

and

(b) a doped silicate layer.

21. (New) The combination according to claim 20, wherein said doped silicate is boron doped glass.

22. (New) The combination according to claim 20, wherein said doped silicate is phosphorous doped glass.

23. (New) The combination according to claim 20, wherein said doped silicate is boron-phosphorous doped glass.

24. (New) The combination according to claim 20, wherein said solvent mixture consists essentially of ethylene glycol and glycerol in a mixing ratio of from 1:10 to 10:1.

25. (New) The combination according to claim 20, wherein said solvent mixture consists essentially of ethylene glycol and glycerol in a mixing ratio of from 1:5 to 5:1.

26. (New) The combination according to claim 20, wherein the amount of said water is 6.4 -20 % by weight.